

“Source/drain materials for Ge nMOS devices: phosphorus activation in epitaxial Si, Ge, Ge_{1-x}Sn_x and Si_yGe_{1-x-y}Sn_x”. Vohra A, Makkonen I, Pourtois G, Slotte J, Porret C, Rosseel E, Khanam A, Tirrito M, Douhard B, Loo R, Vandervorst W, Ecs Journal Of Solid State Science And Technology **9**, 044010 (2020). <http://doi.org/10.1149/2162-8777/AB8D91>